

ABSTRACT OF THE DISCLOSURE

In order to provide an anticorrosive technique

for metal wirings formed by a chemical mechanical

5 polishing (CMP) method, a process for manufacturing a
semiconductor integrated circuit device according to

the invention comprises the steps of: forming a metal

layer of Cu (or a Cu alloy containing Cu as a main

component) over the major face of a wafer and then

10 planarizing the metal layer by a chemical mechanical
polishing (CMP) method to form metal wirings;

anticorrosing the planarized major face of the wafer

to form a hydrophobic protective film over the

surfaces of the metal wirings; immersing the

15 anticorroded major face of the wafer or keeping the
same in a wet state so that it may not become dry; and
post-cleaning the major face, kept in the wet state,
of the wafer.